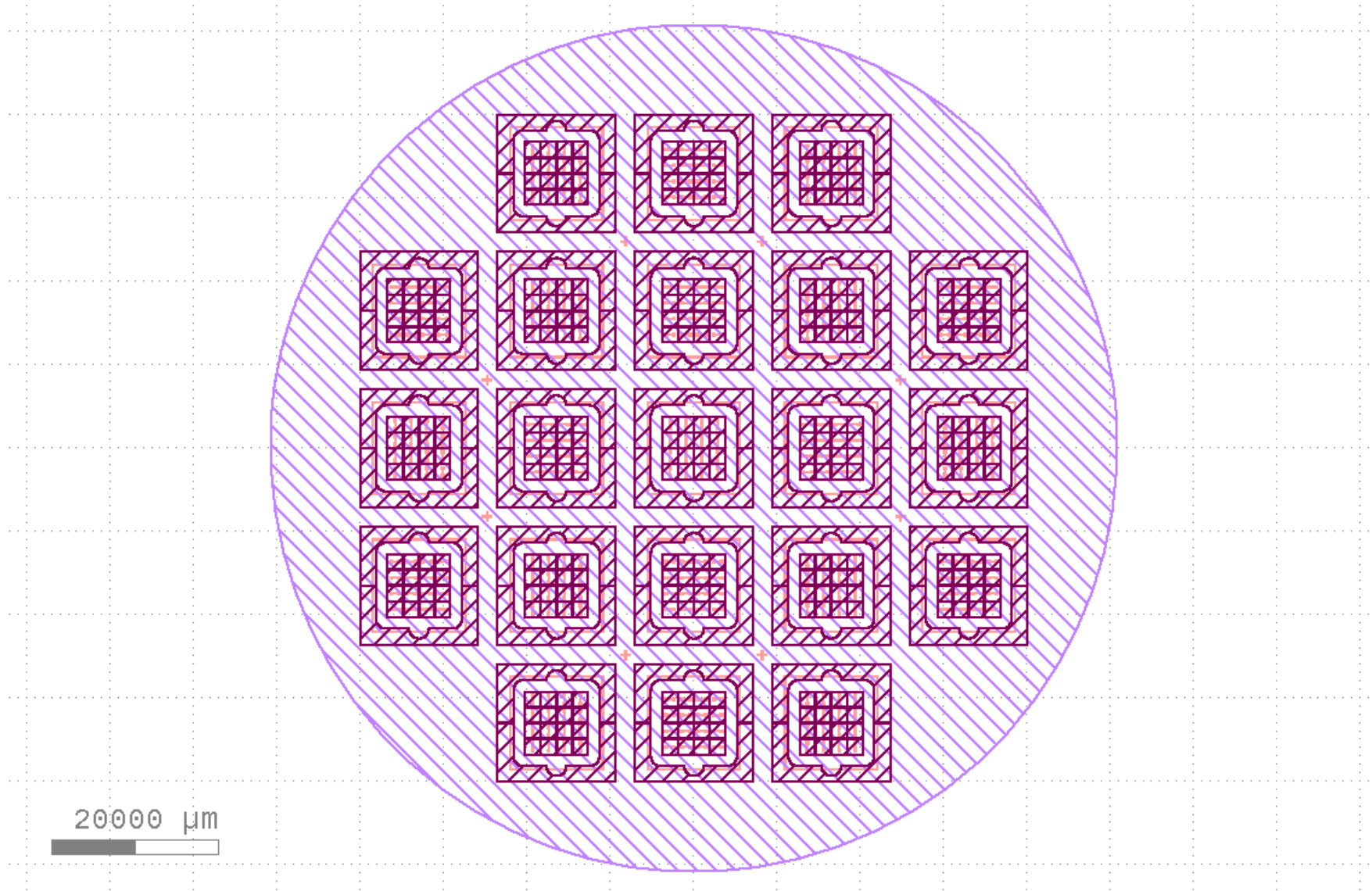


Growth and Characterization of Superconducting Josephson Junctions in Low-Temperature MBE

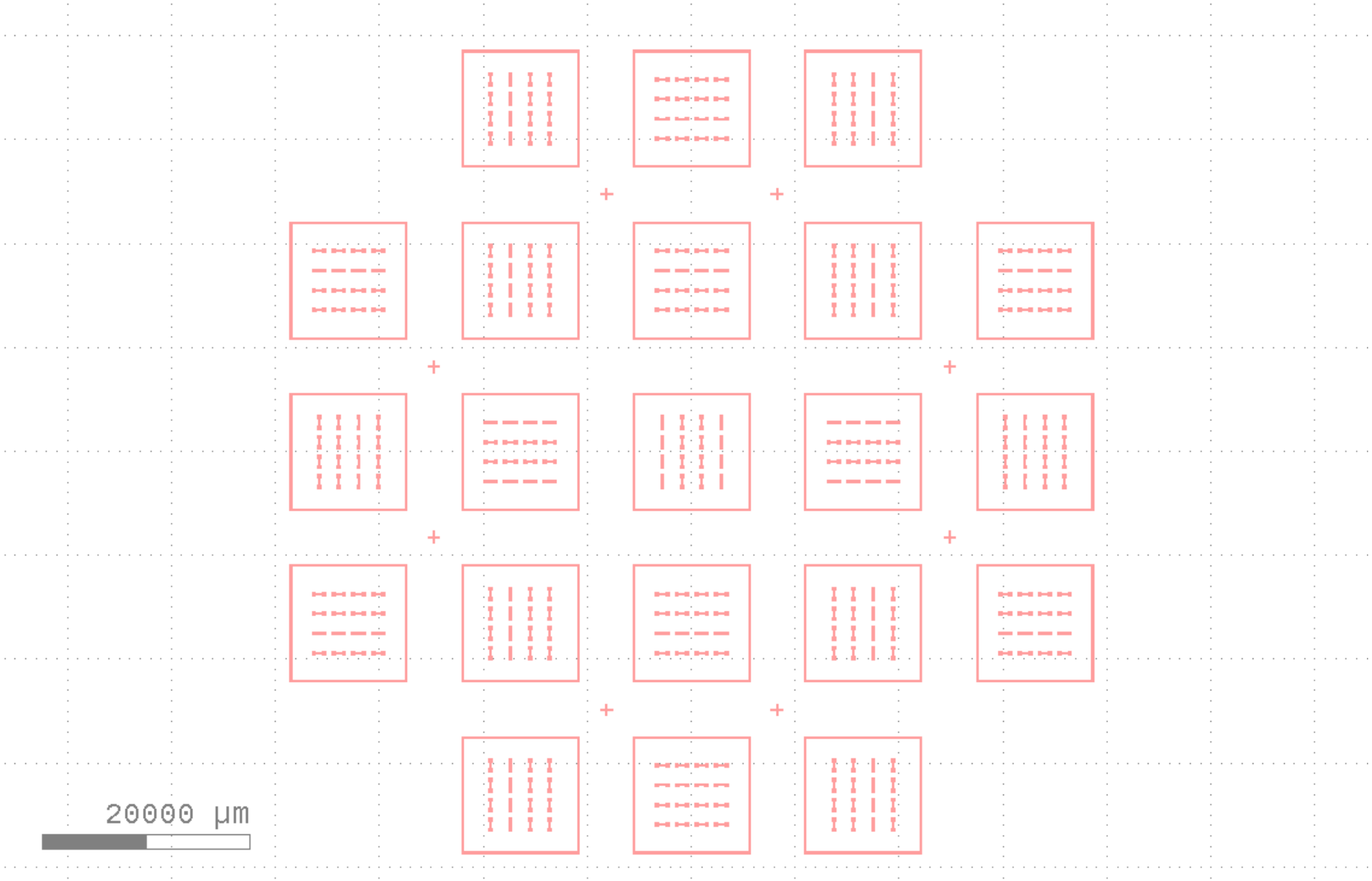
Shirshendu Chatterjee

Design of the Shadow Mask for the Josephson Junctions

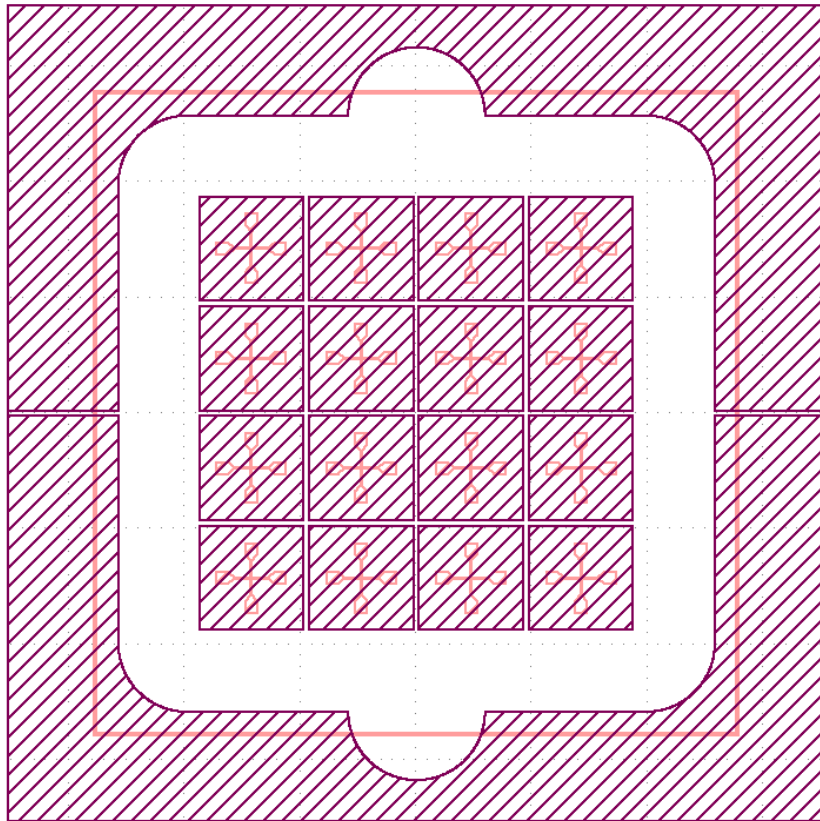
Shadow Mask – Design 1.



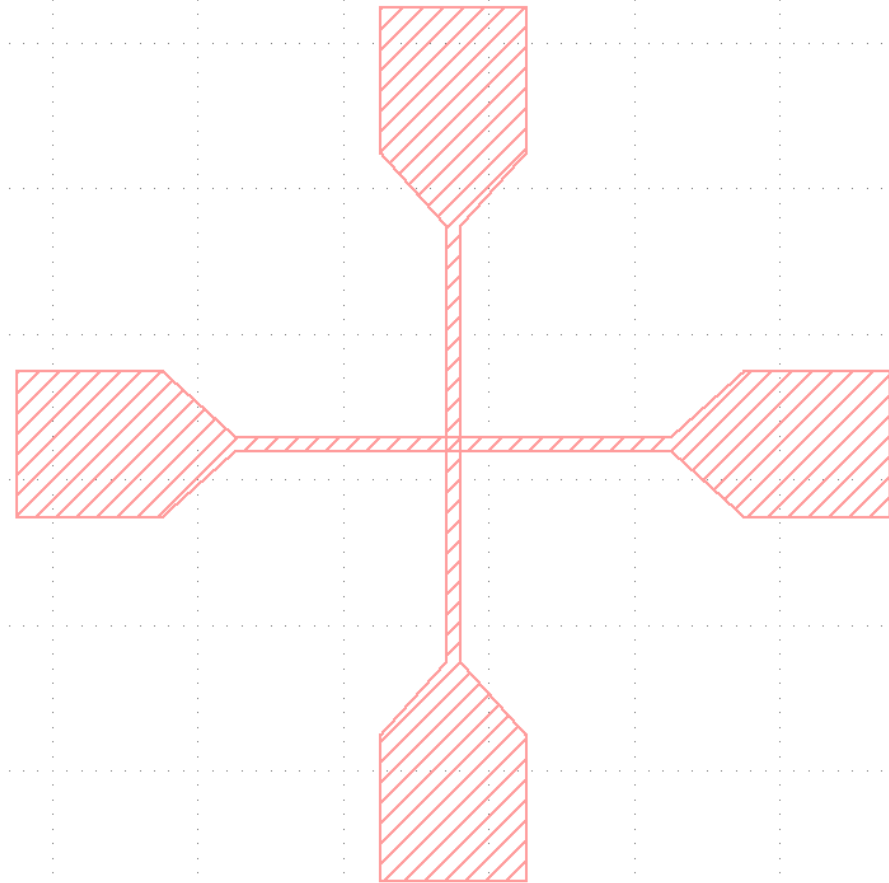
Lithography Design – 1.



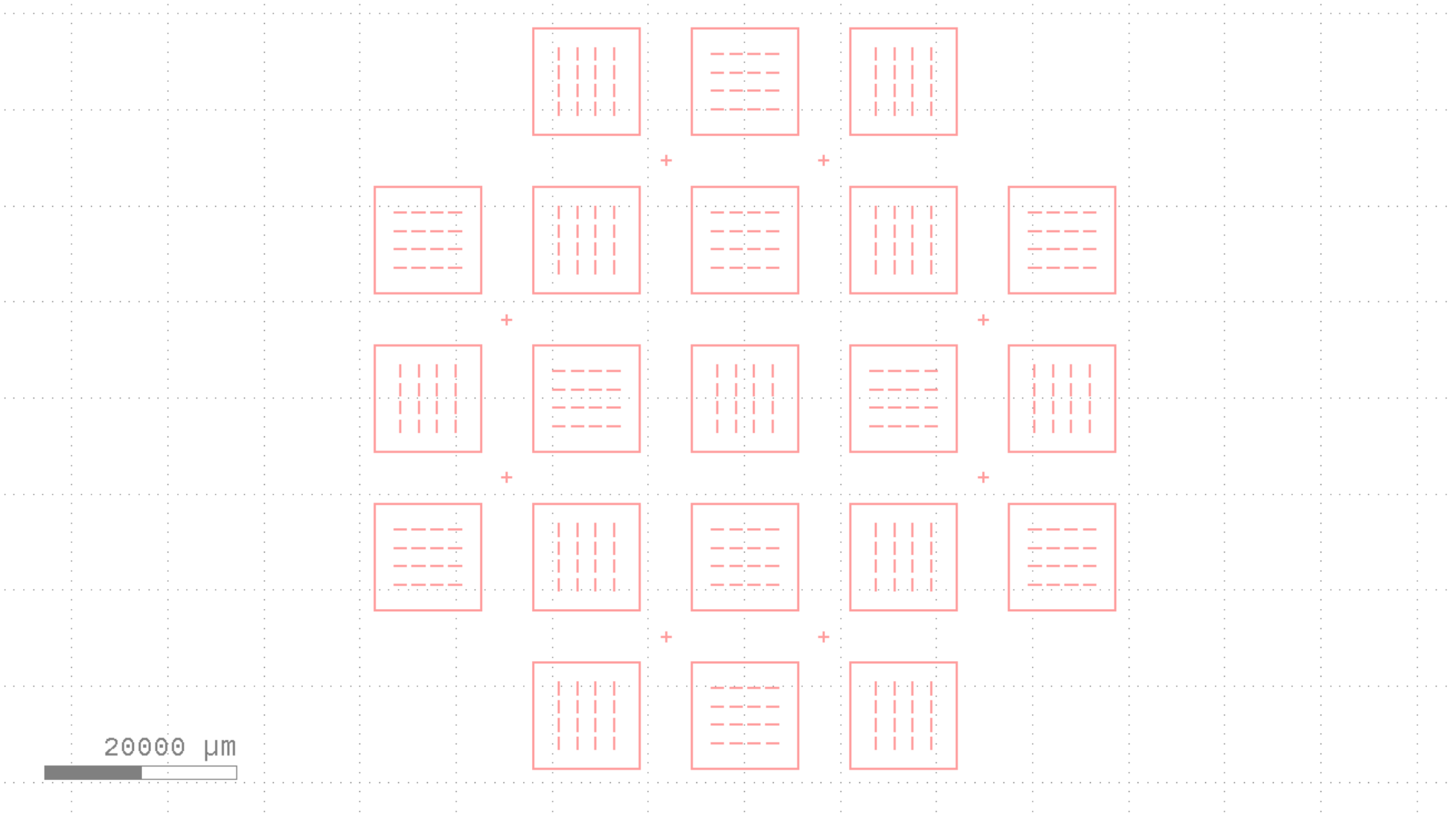
Josephson Junction - 2



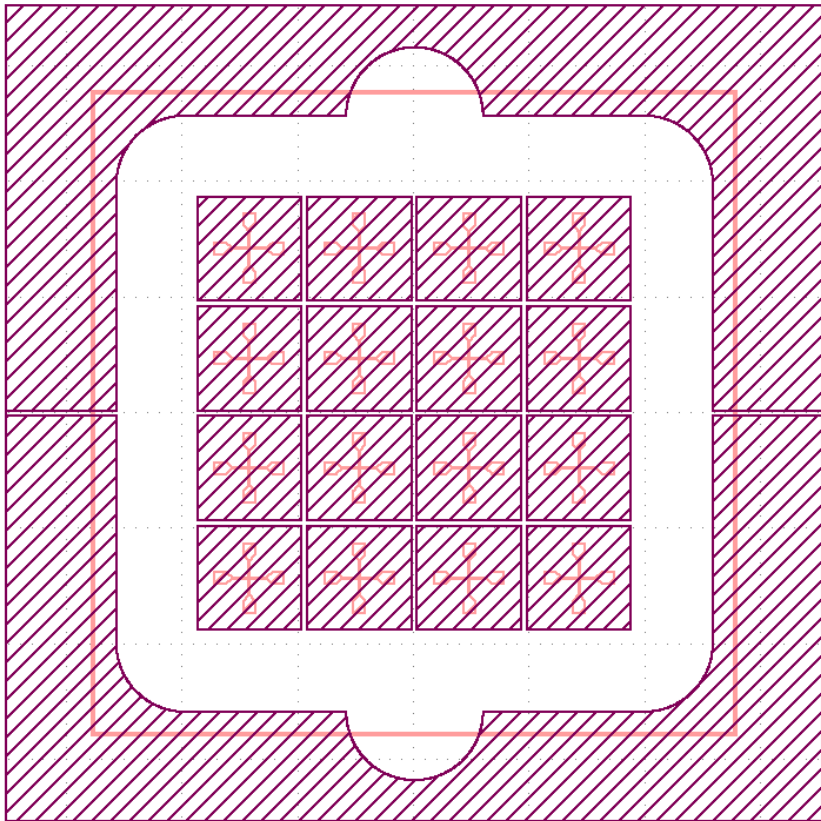
400 μm



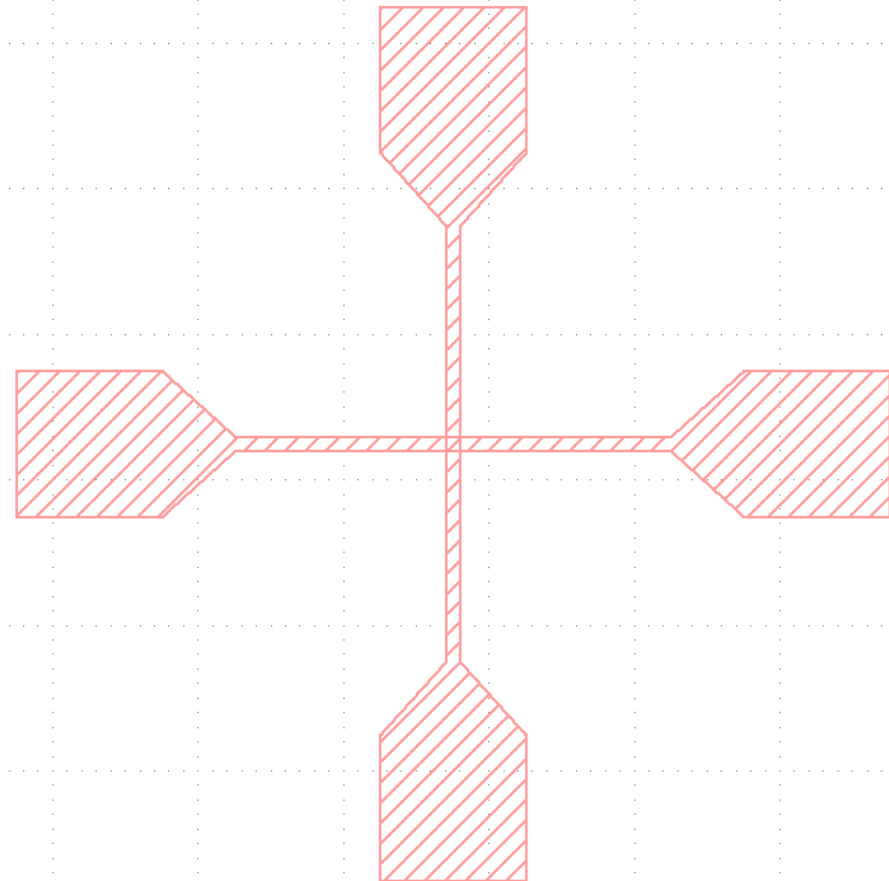
Lithography Design – 2.



Josephson Junction - 2



400 μm

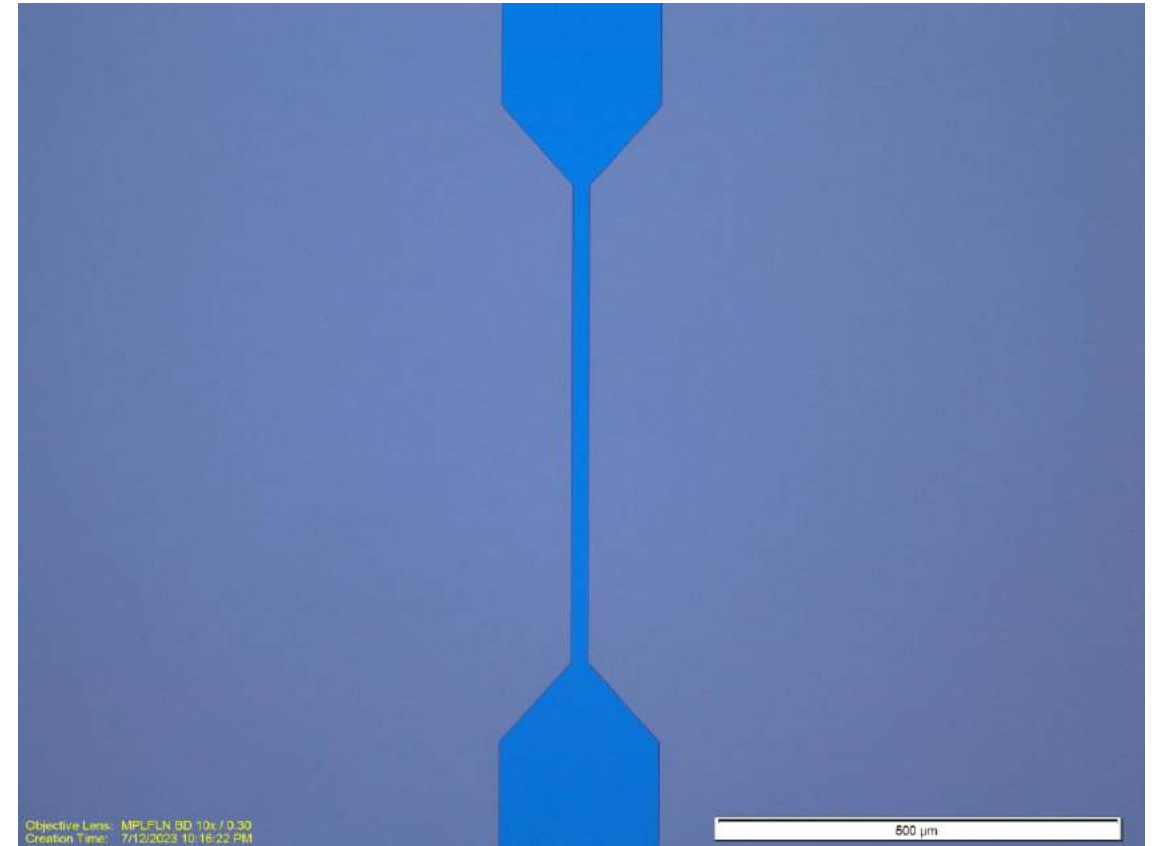
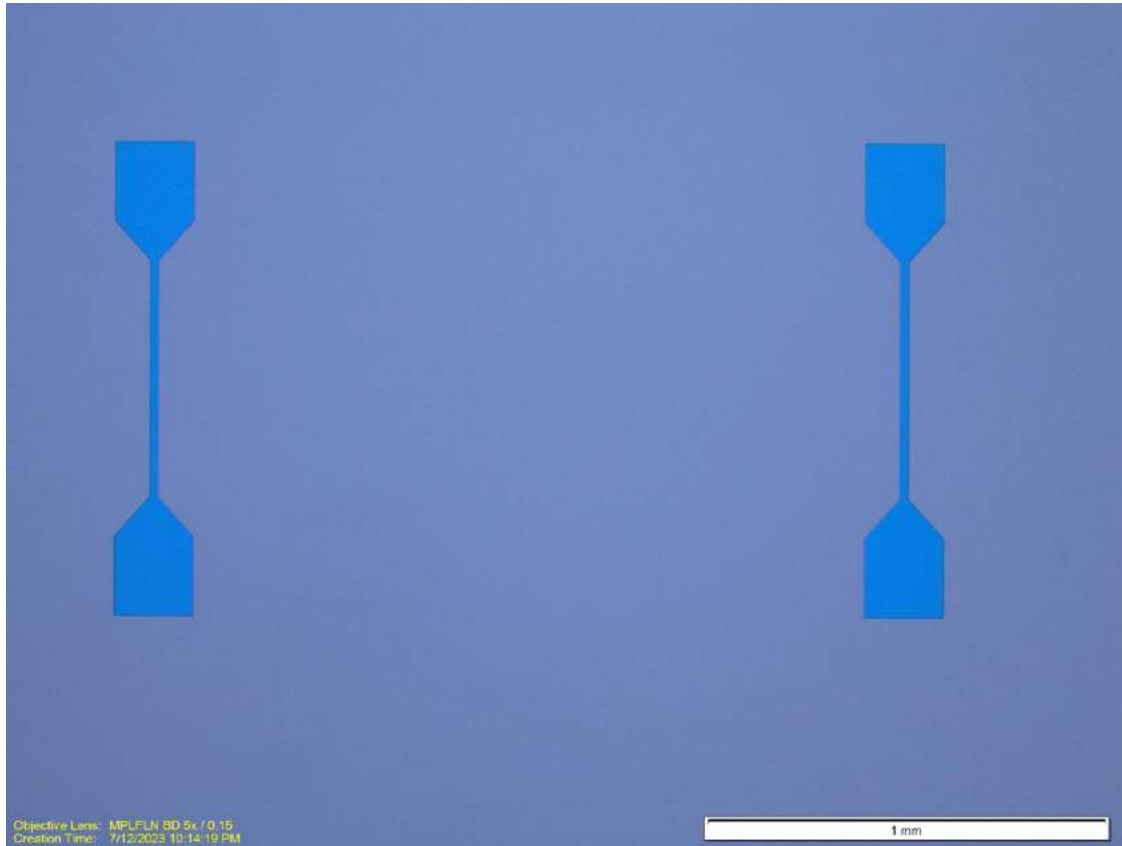


Patterning the Top Layers

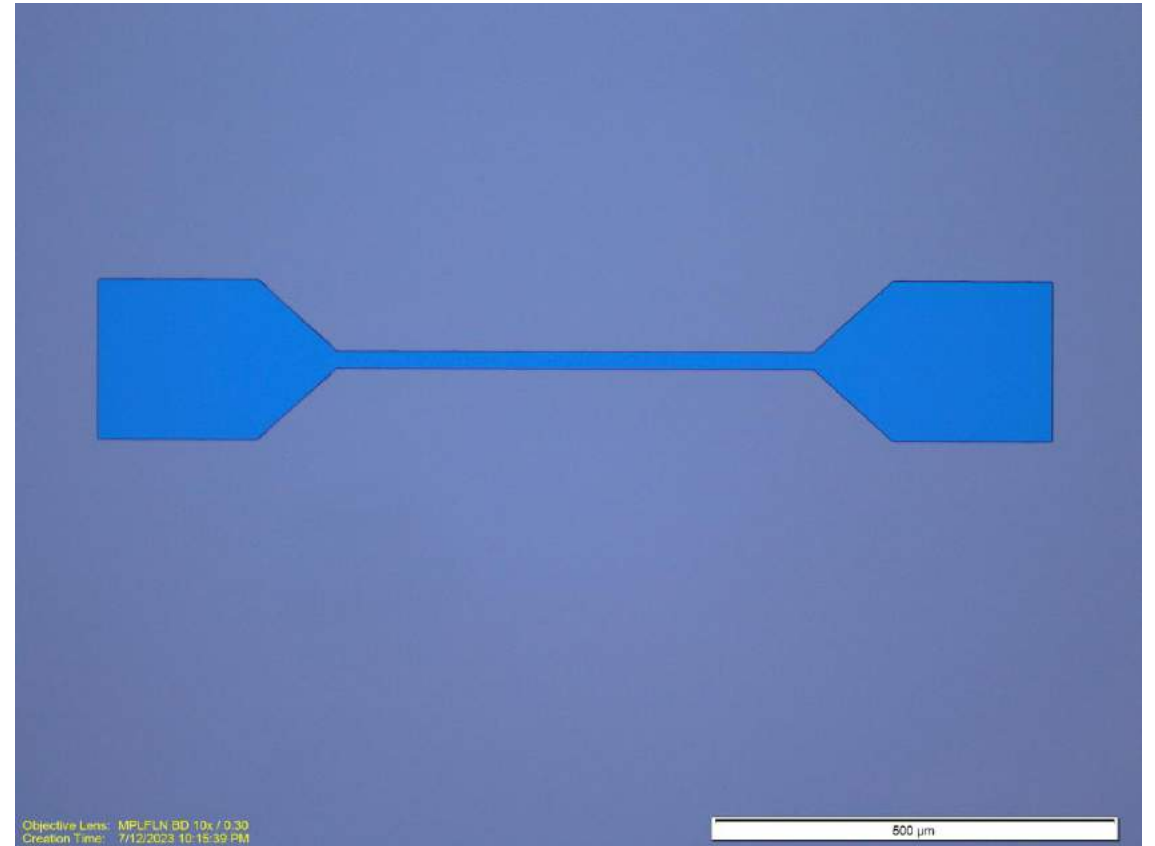
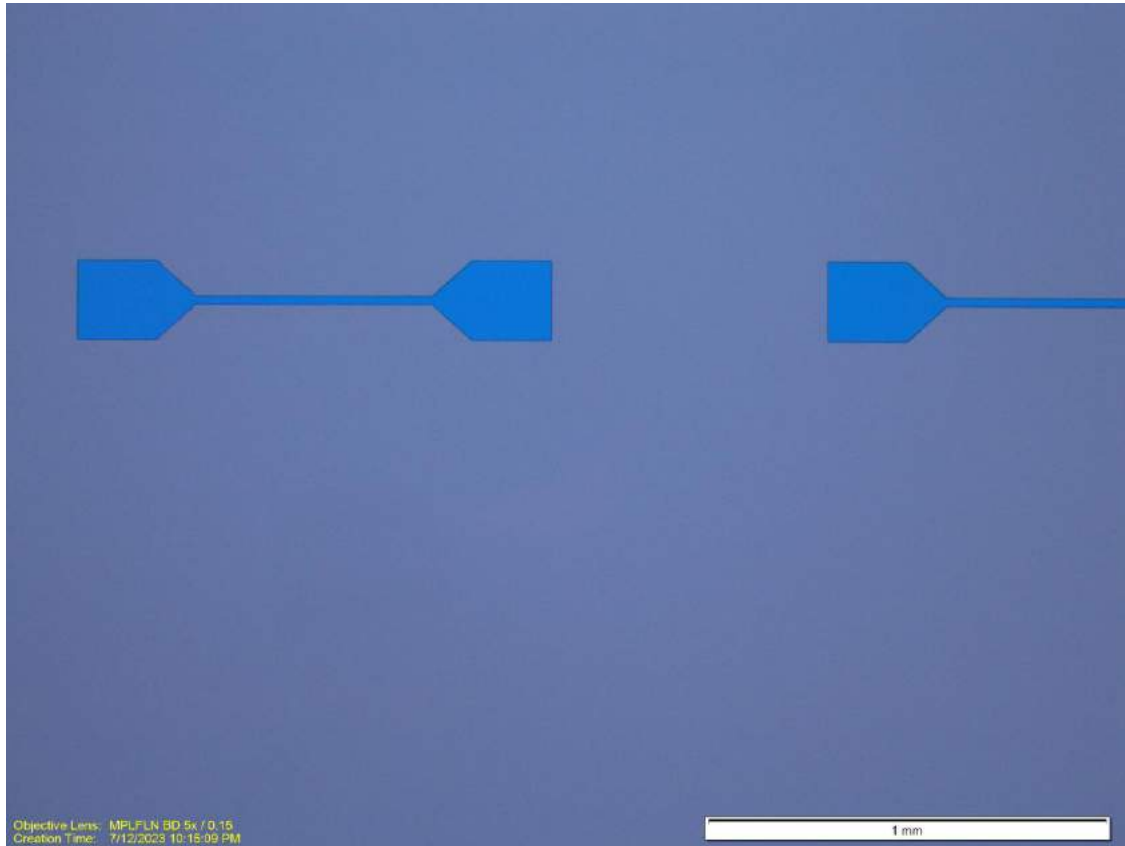
Recipe – 1st Lithography

1. 2 min Acetone in USW
2. 2 min Isopropanol in USW
3. PE II at 300mTorr and 100 Watts O₂ for 15 secs.
4. Spin resist AZ4110 at 4krpm for 30s ~ **1.2um thick**
5. Soft bake for 60 sec at 95C
6. MLA: **405nm** Laser, dose **300** mJ/cm² and defocus **4**
7. AZ400K 1:4 developer for 60 sec
8. DI for 60 sec

After 1st Lithography



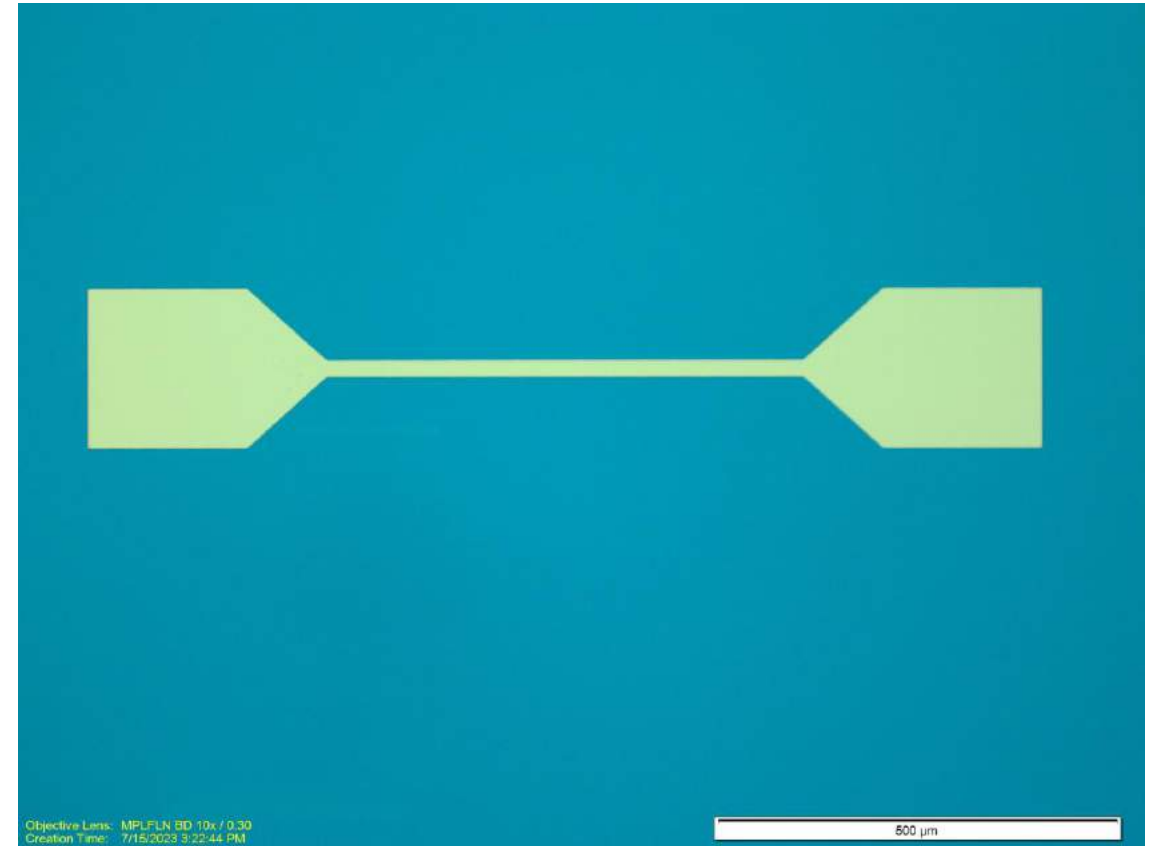
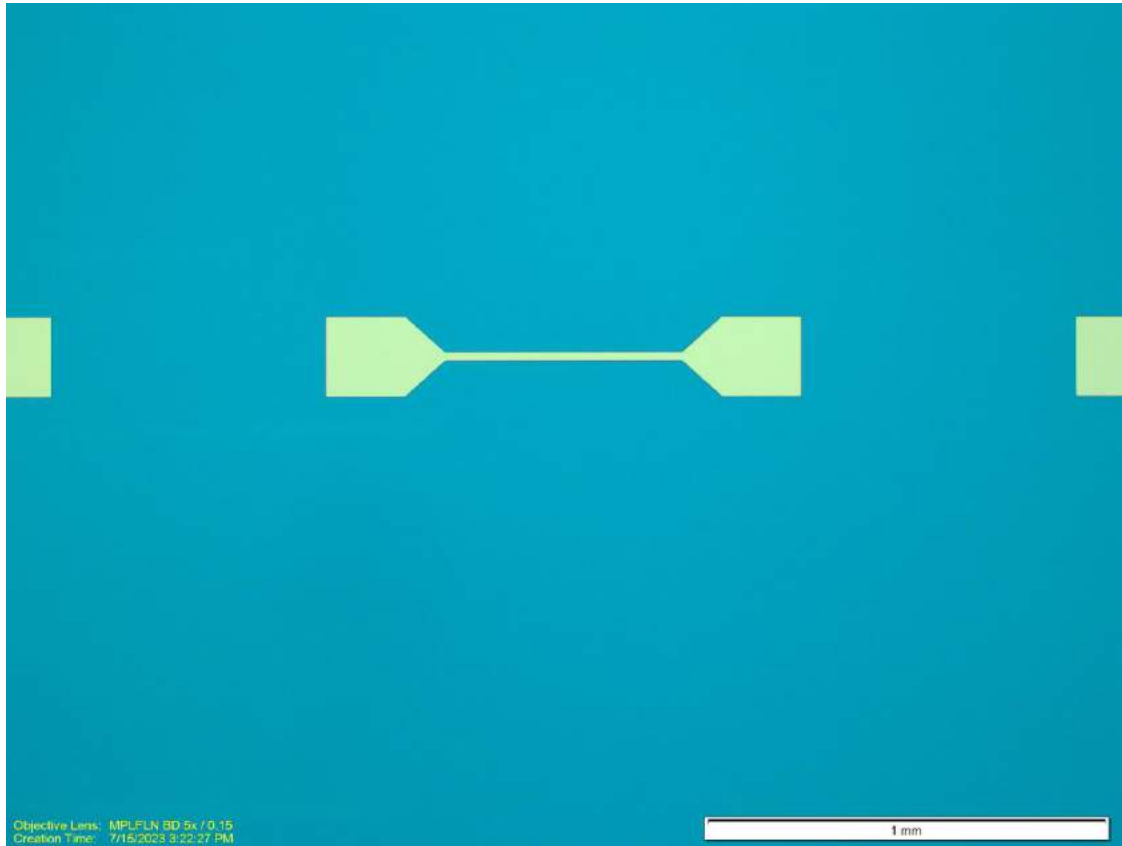
After 1st Lithography



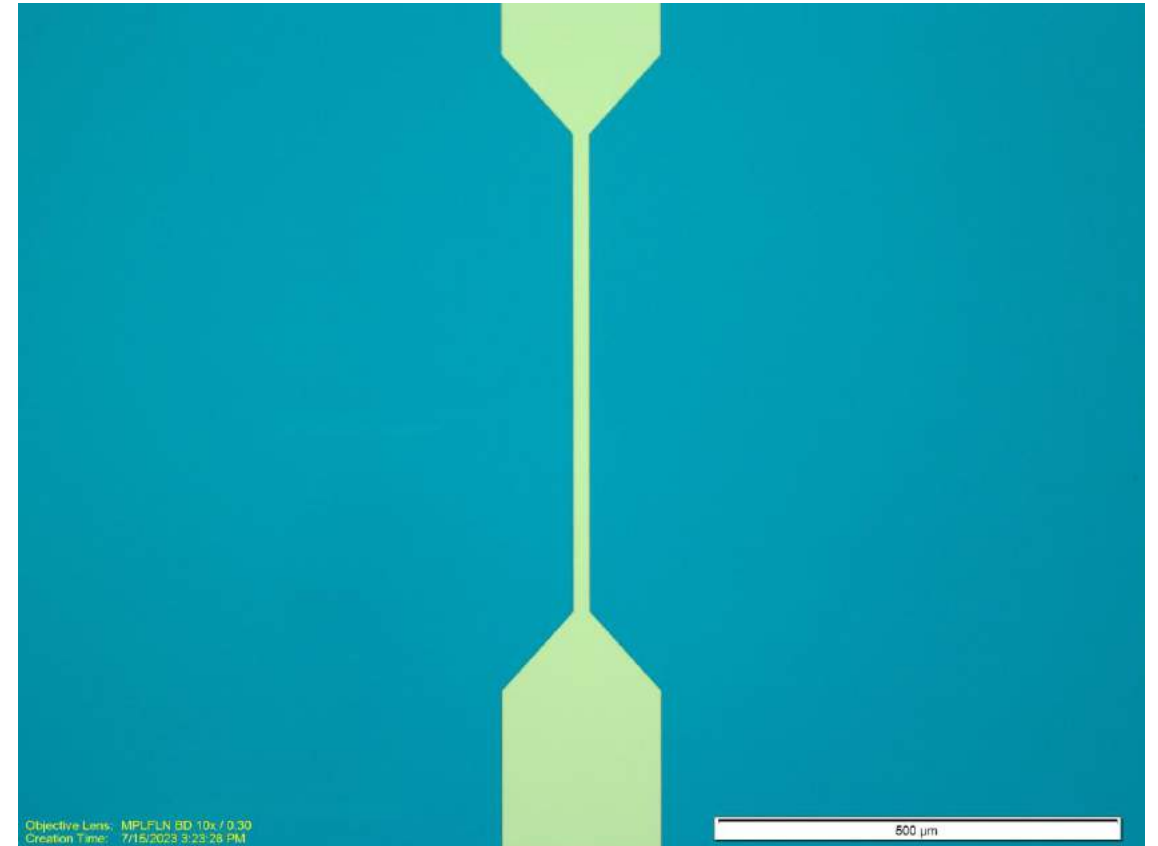
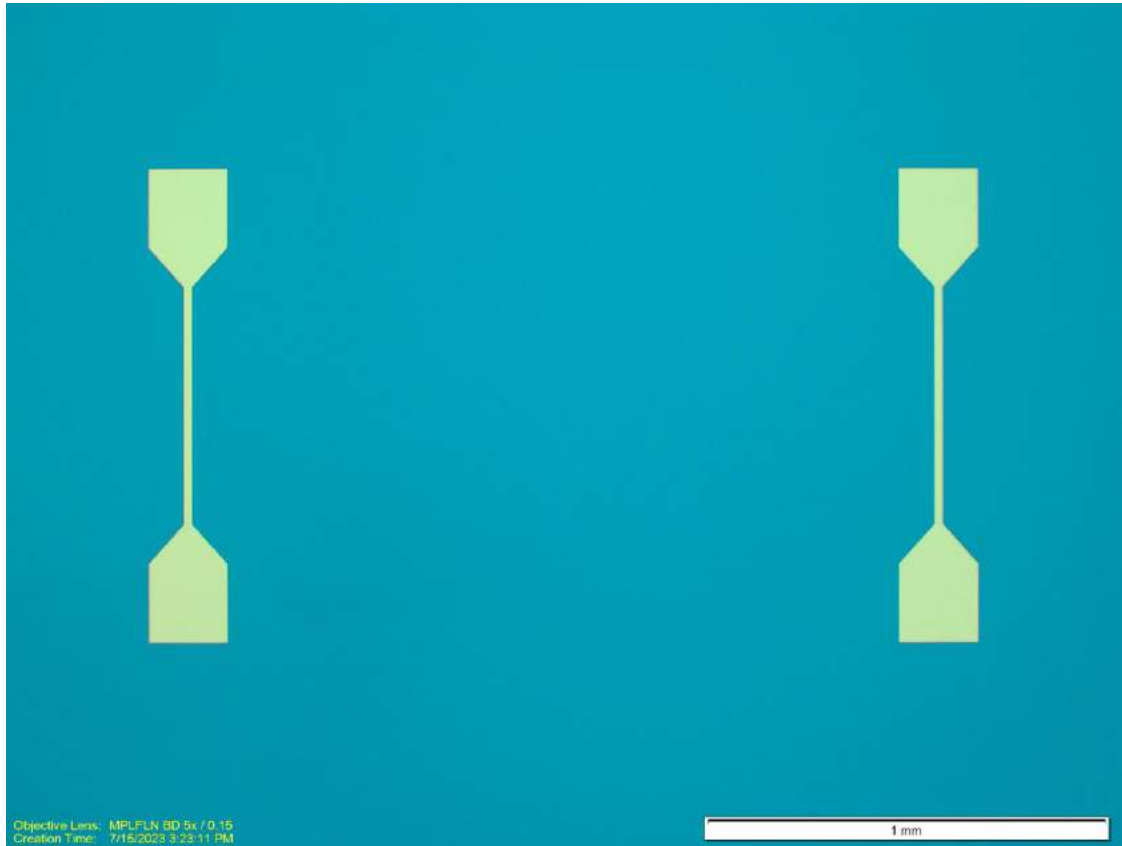
Recipe – Dry Etch and PECVD

1. PE II 300/100 O₂ for 15 sec
2. ICP #1 – O₂ clean for 5 min
 - CF₄/O₂ coat for 2 min
 - CF₄/O₂ etch for 4 min
 - O₂ clean for 5 min

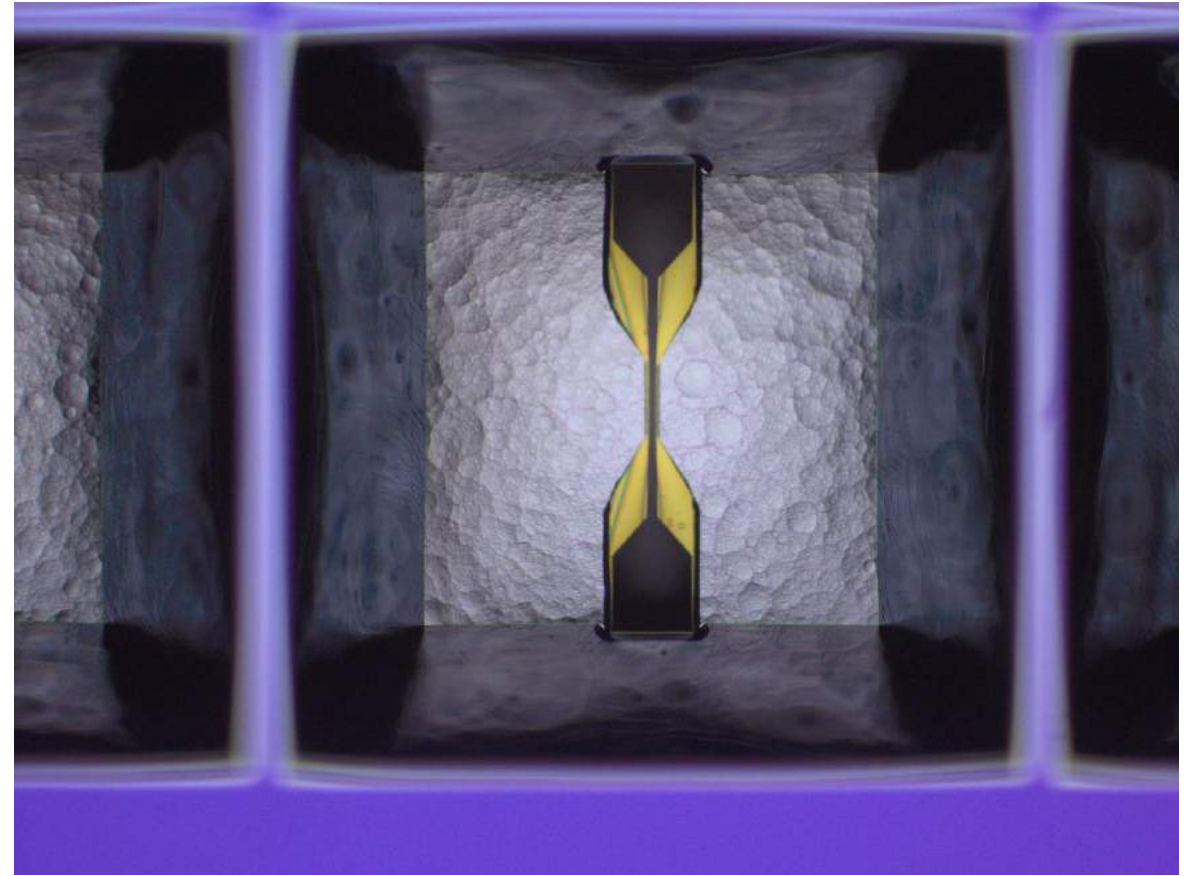
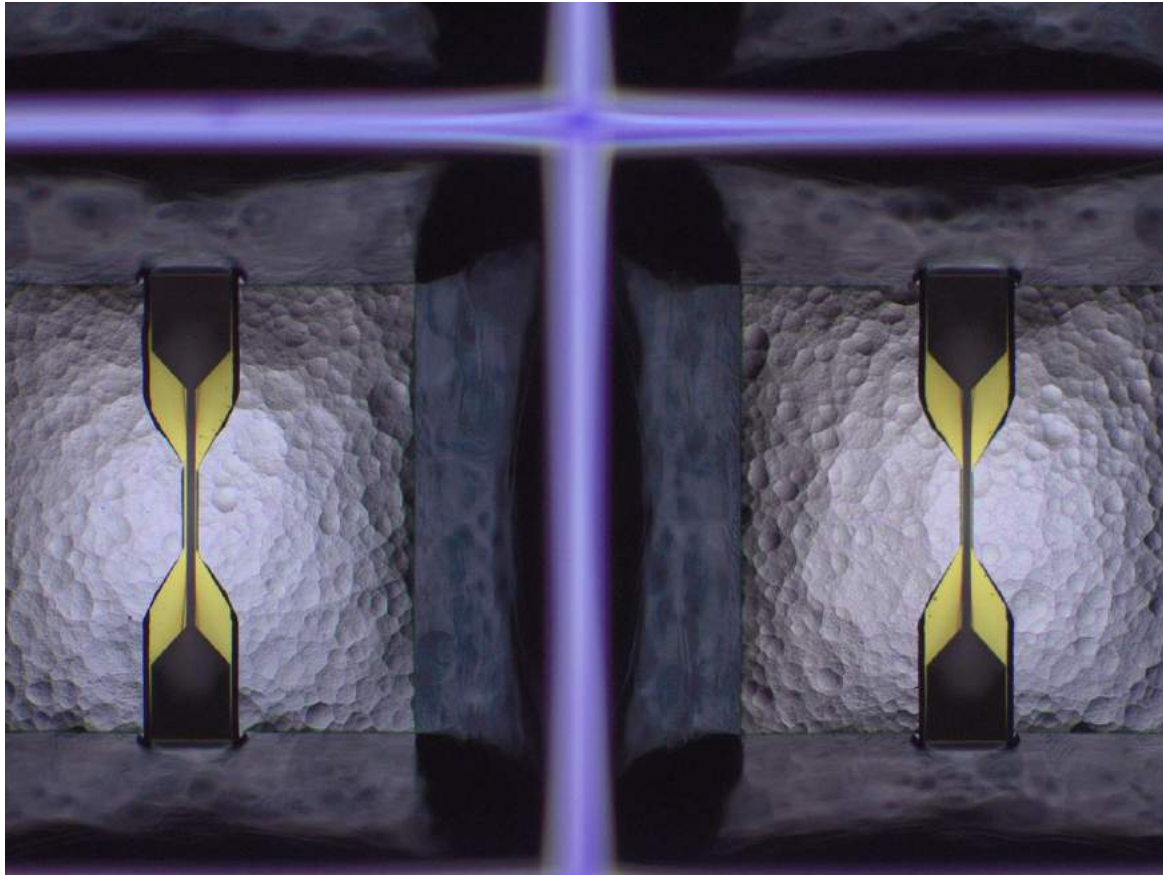
After Dry Etch



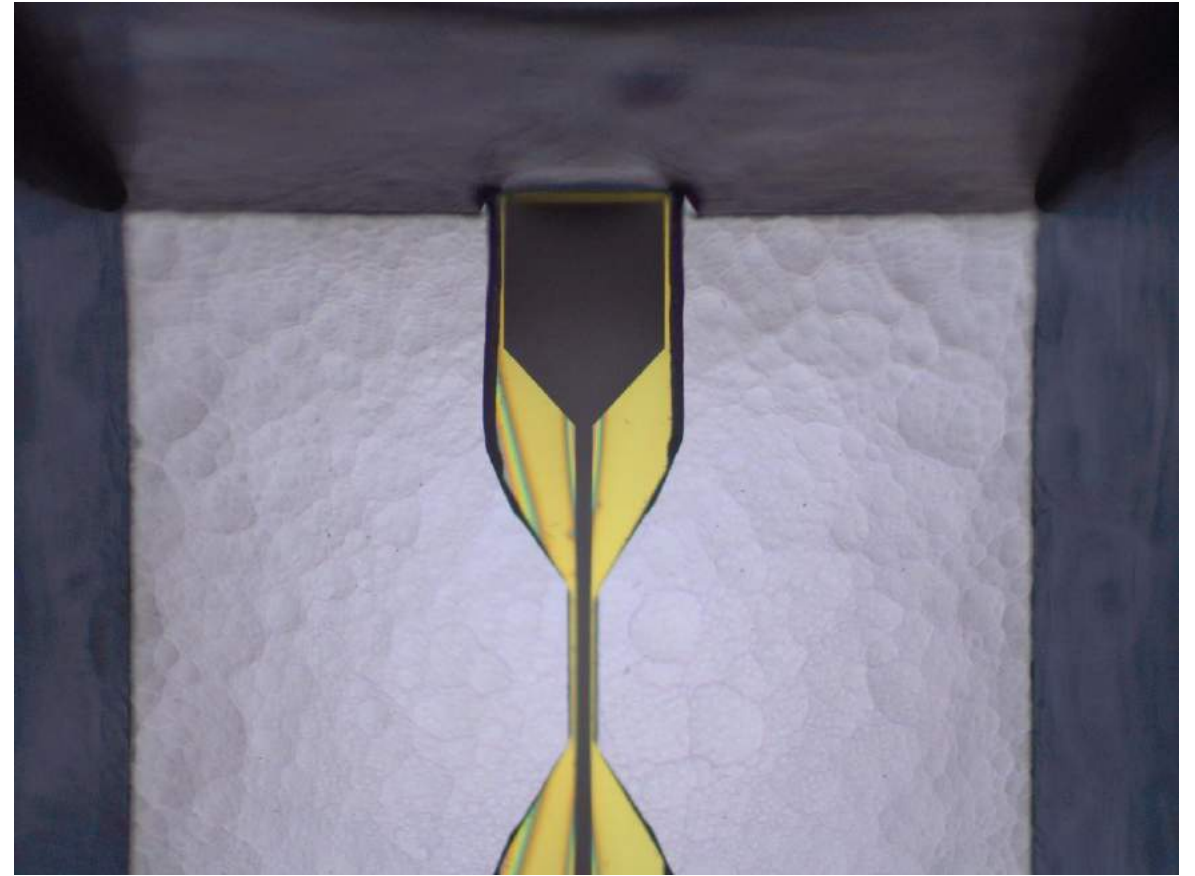
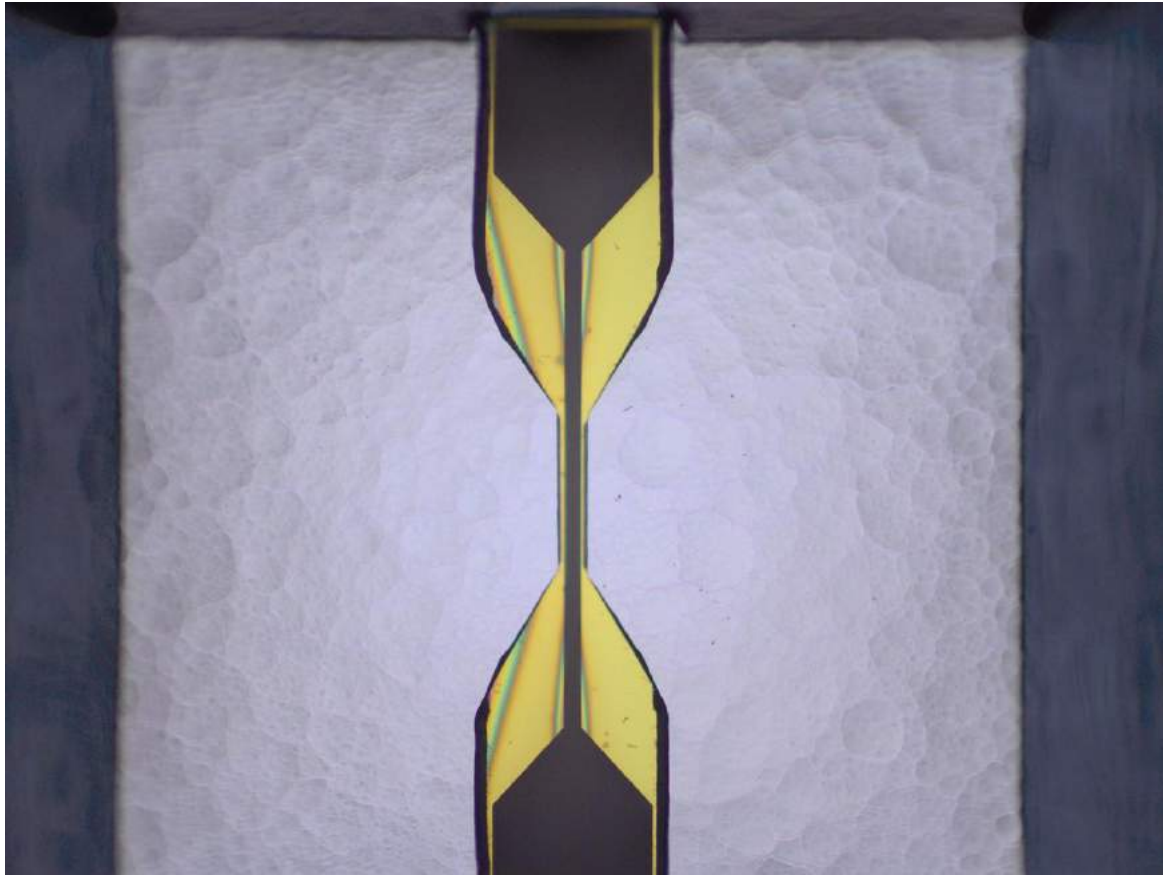
After Dry Etch



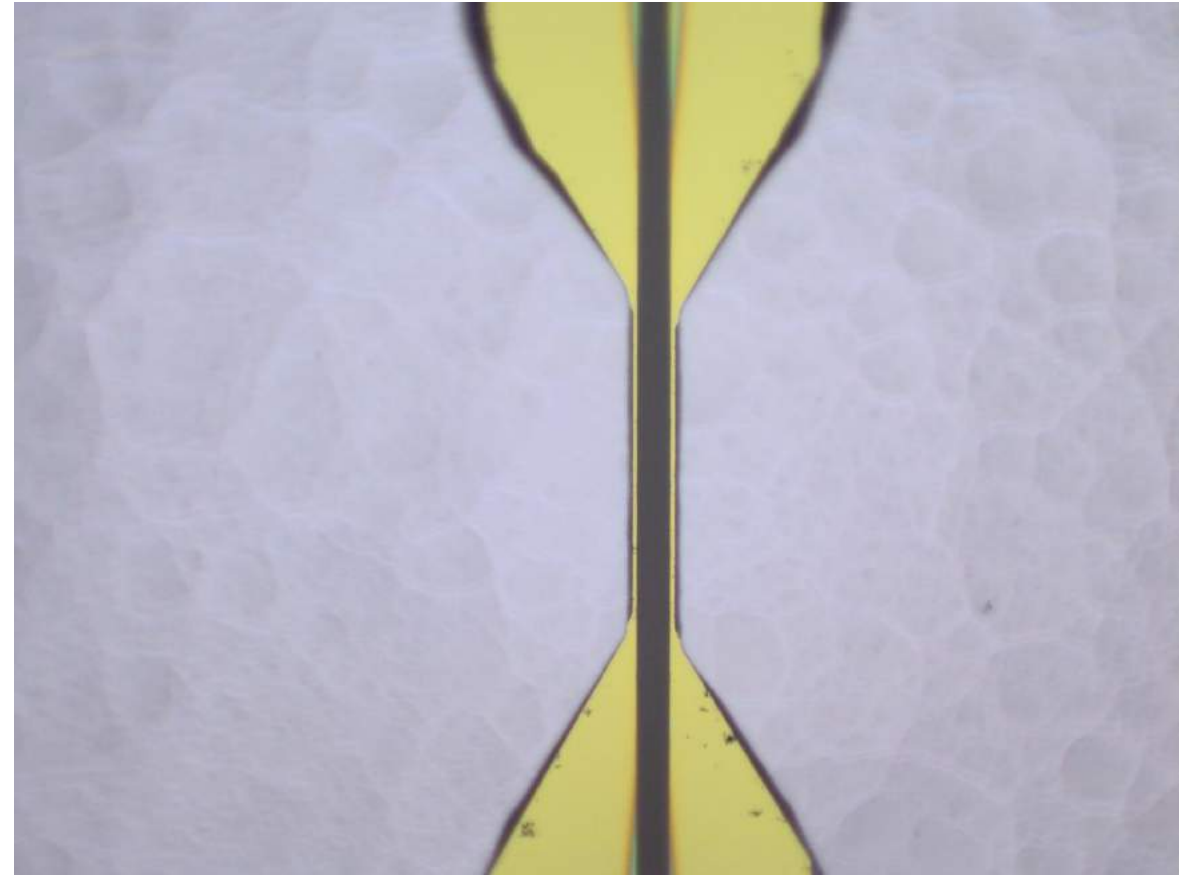
After Final KOH etch



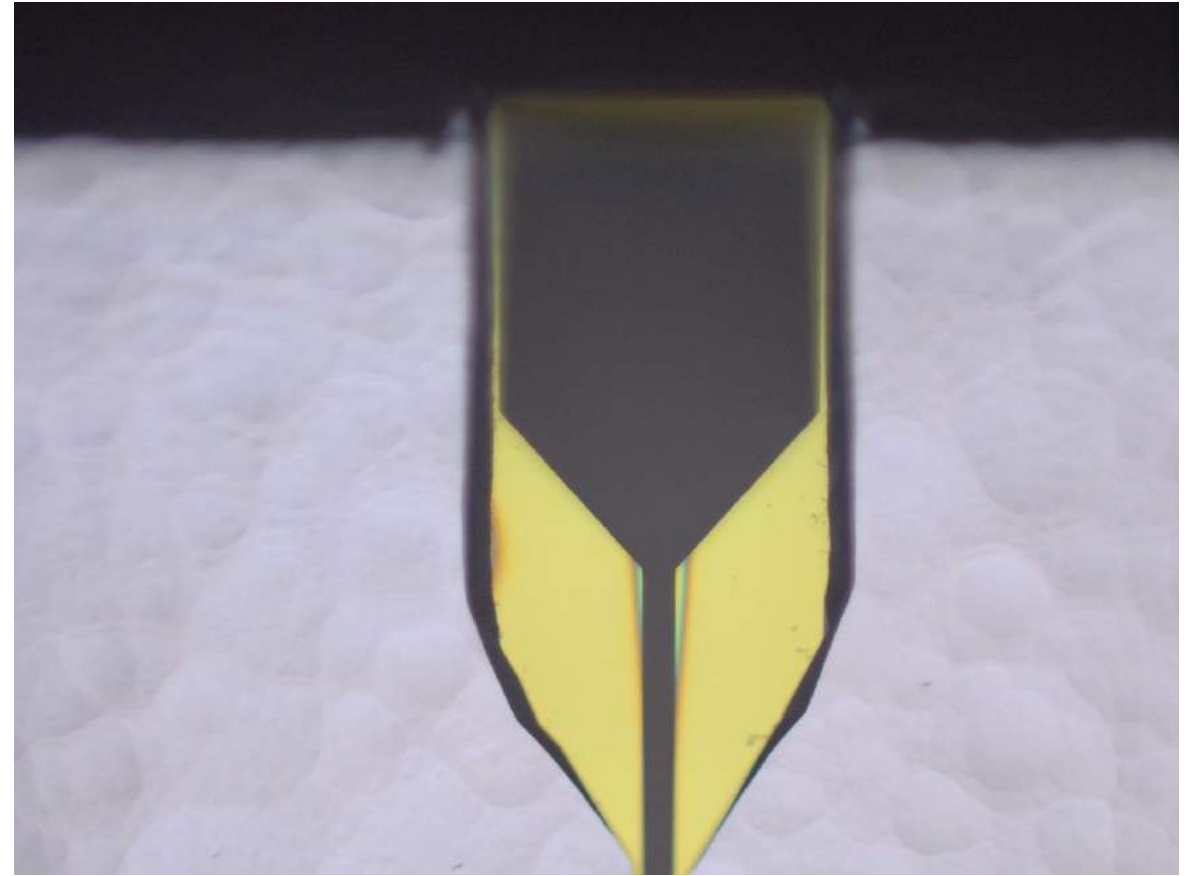
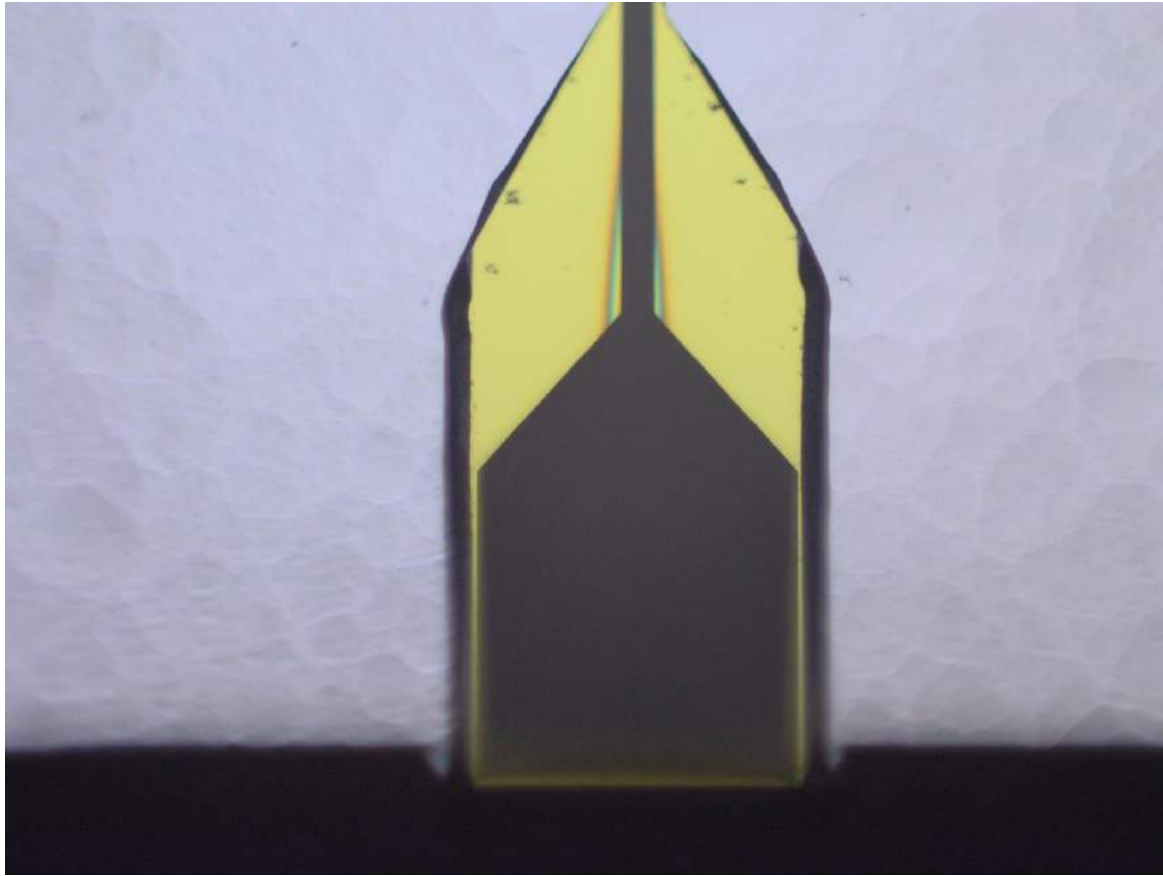
After Final KOH etch



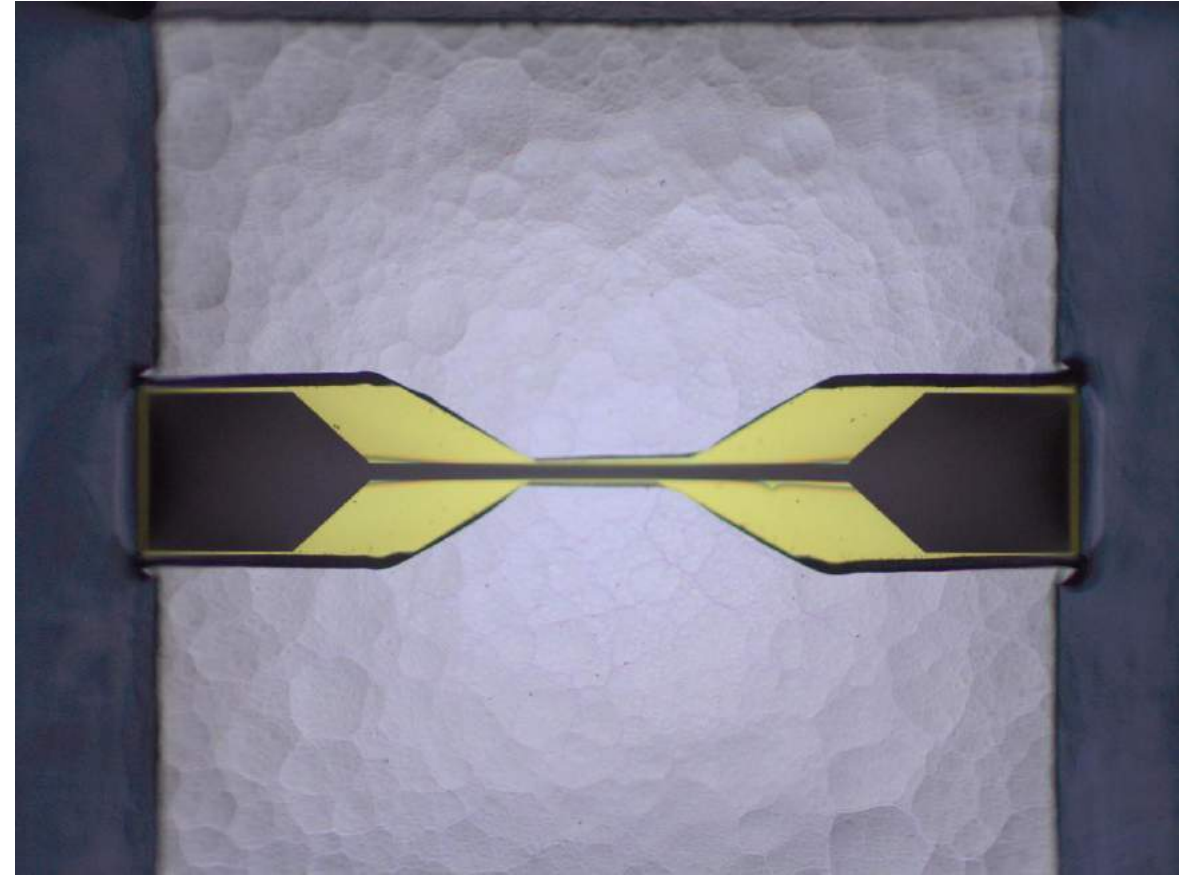
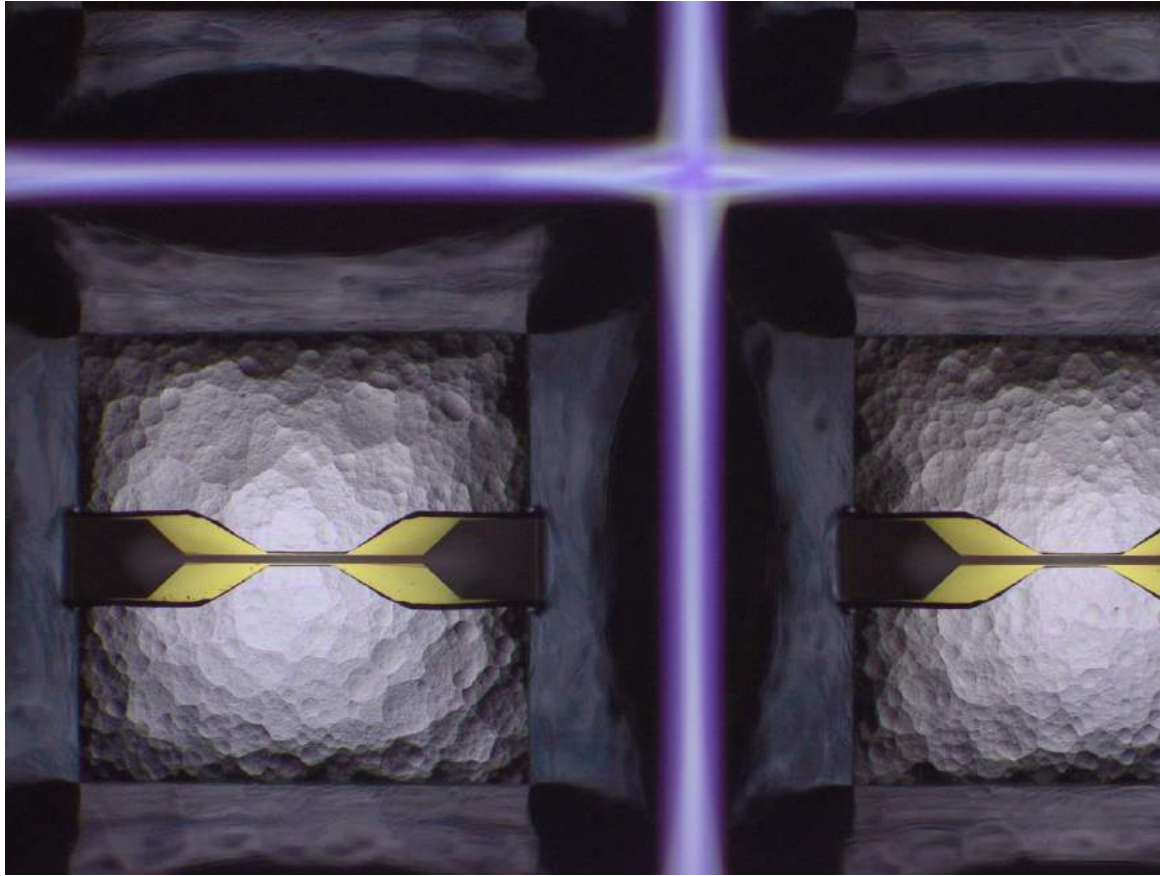
After Final KOH etch



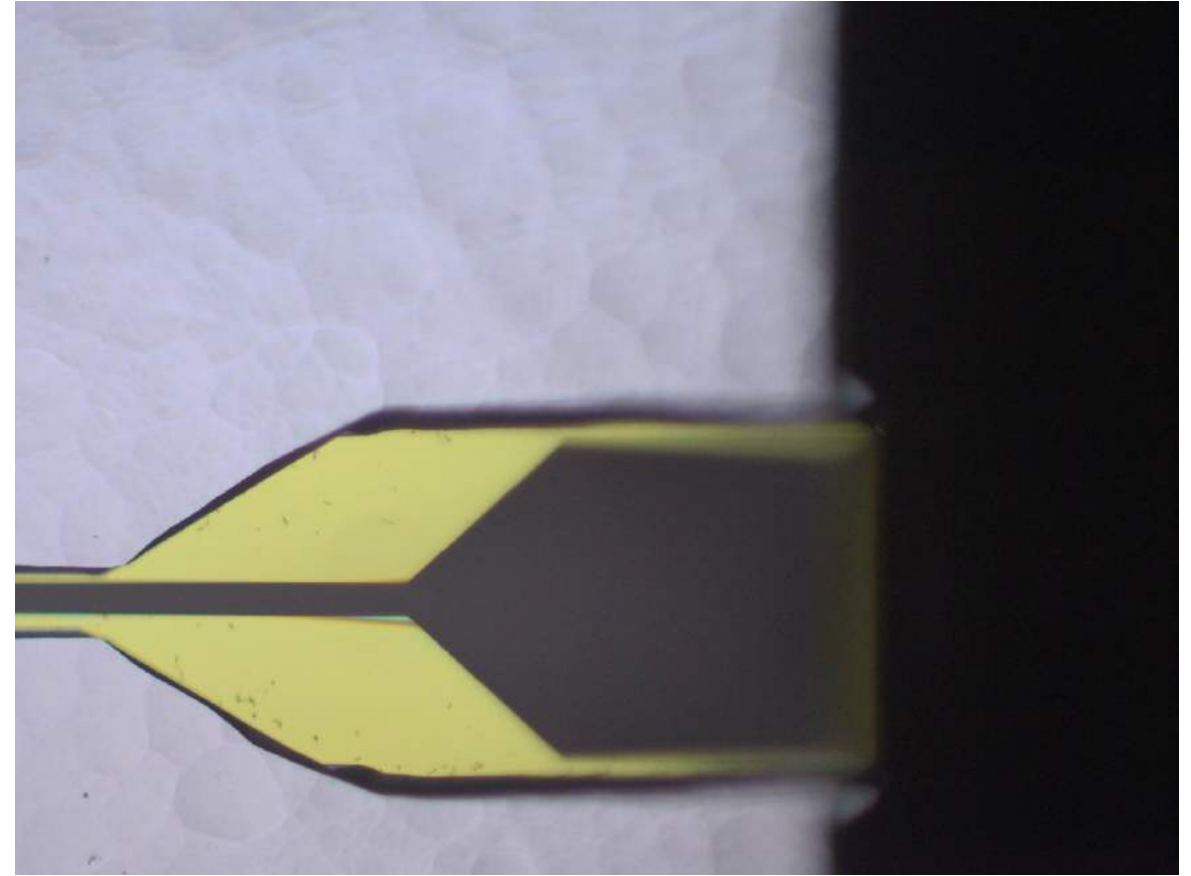
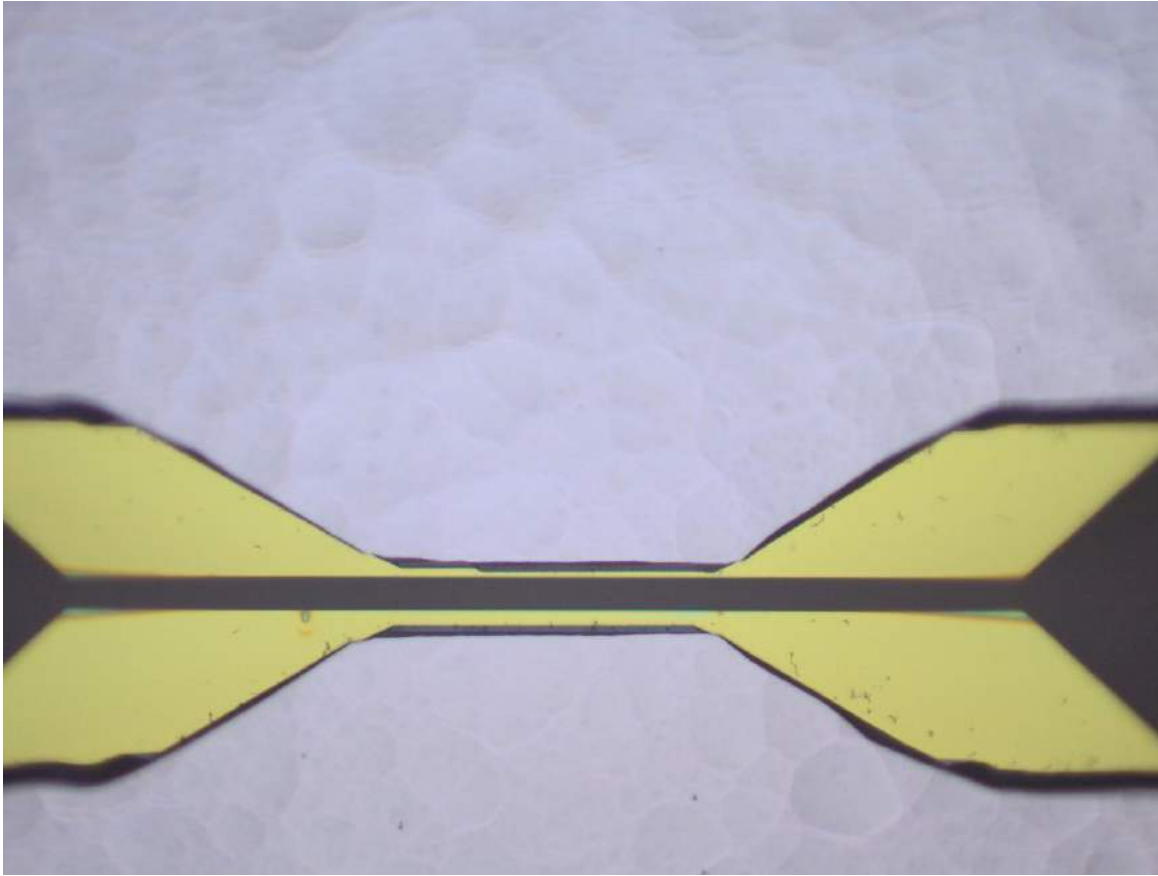
After Final KOH etch



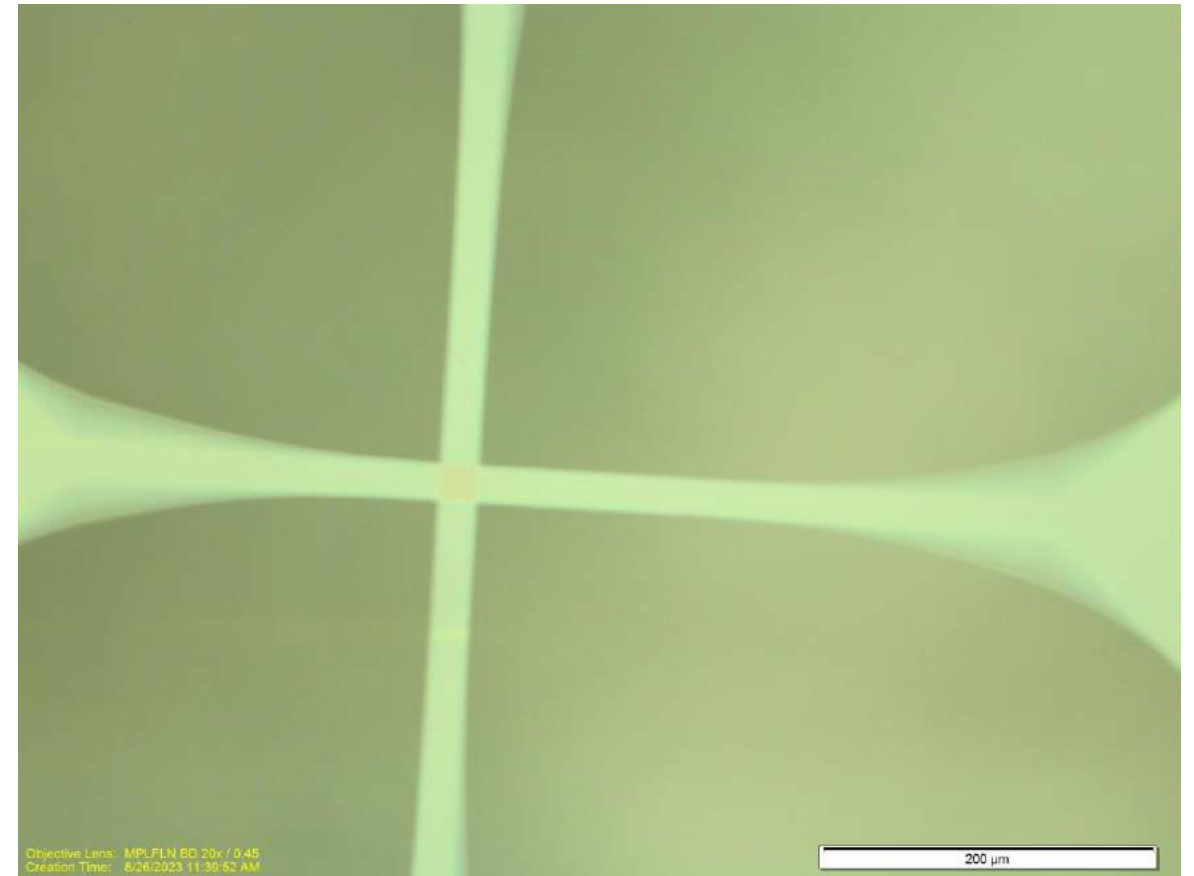
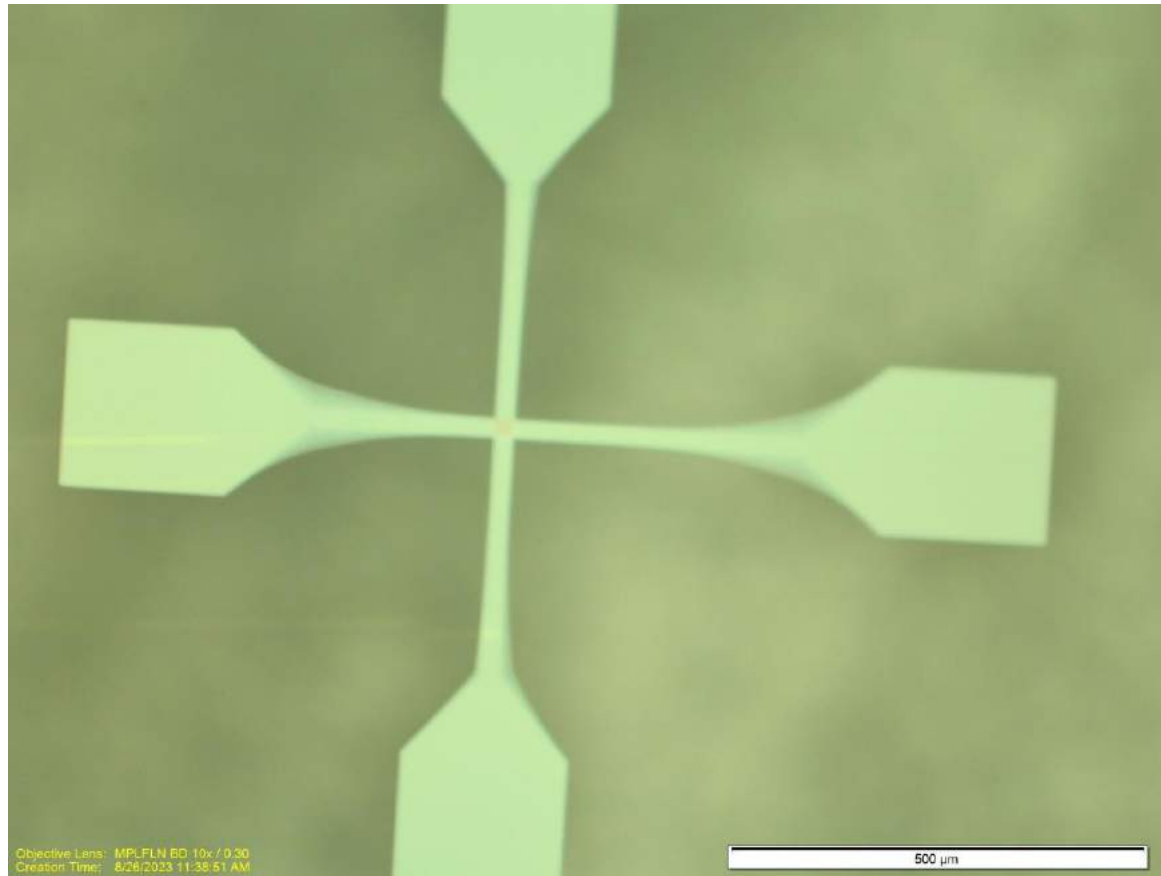
After Final KOH etch



After Final KOH etch



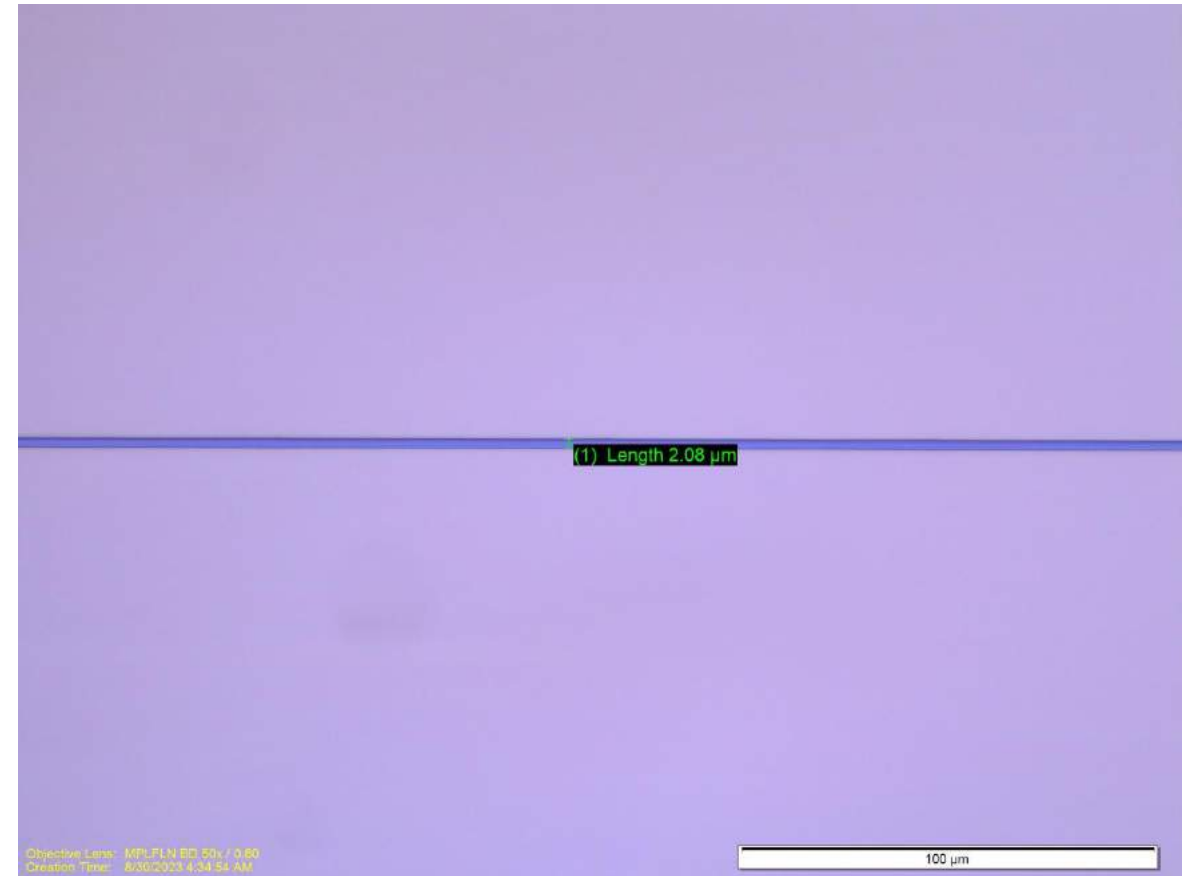
Growth of Ta/Ta₂O₅/Ta Josephson Junctions



Growth of Ta/Ta₂O₅/Ta Josephson Junctions



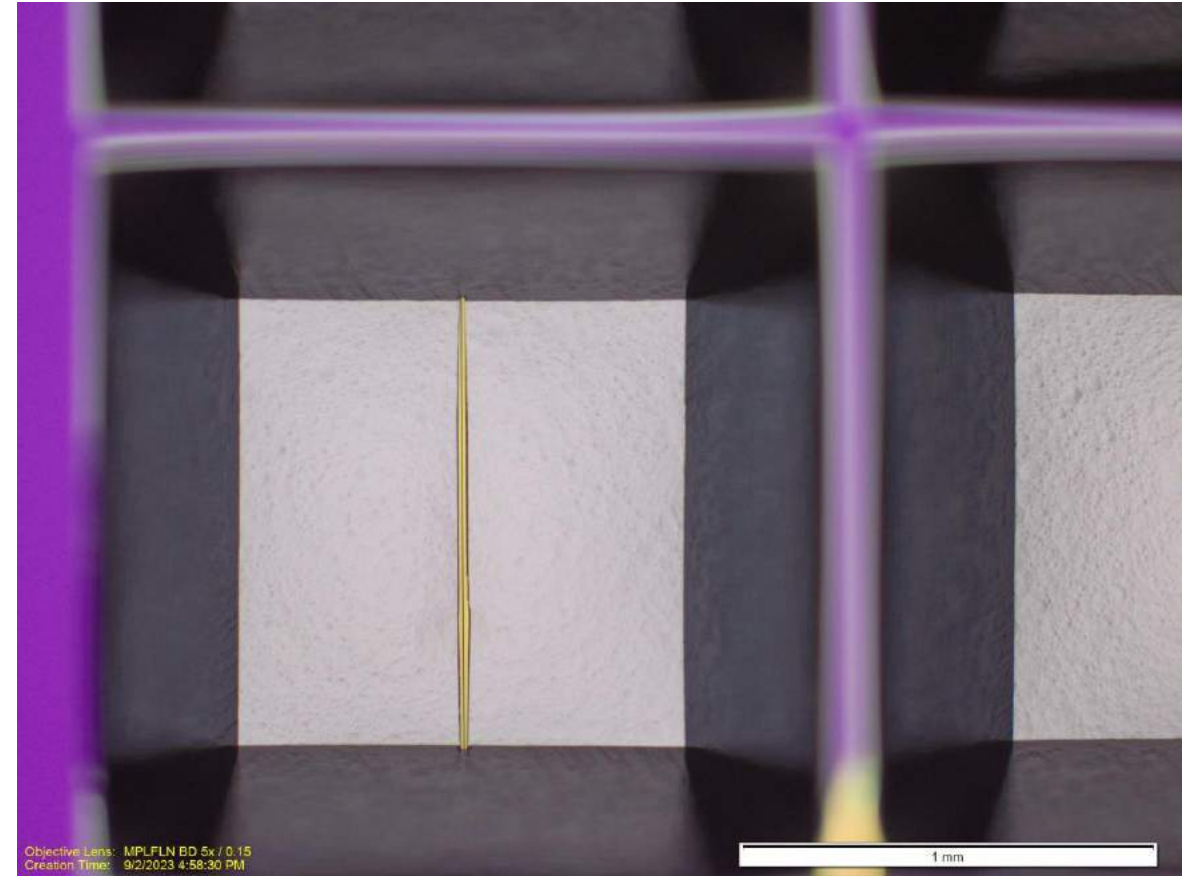
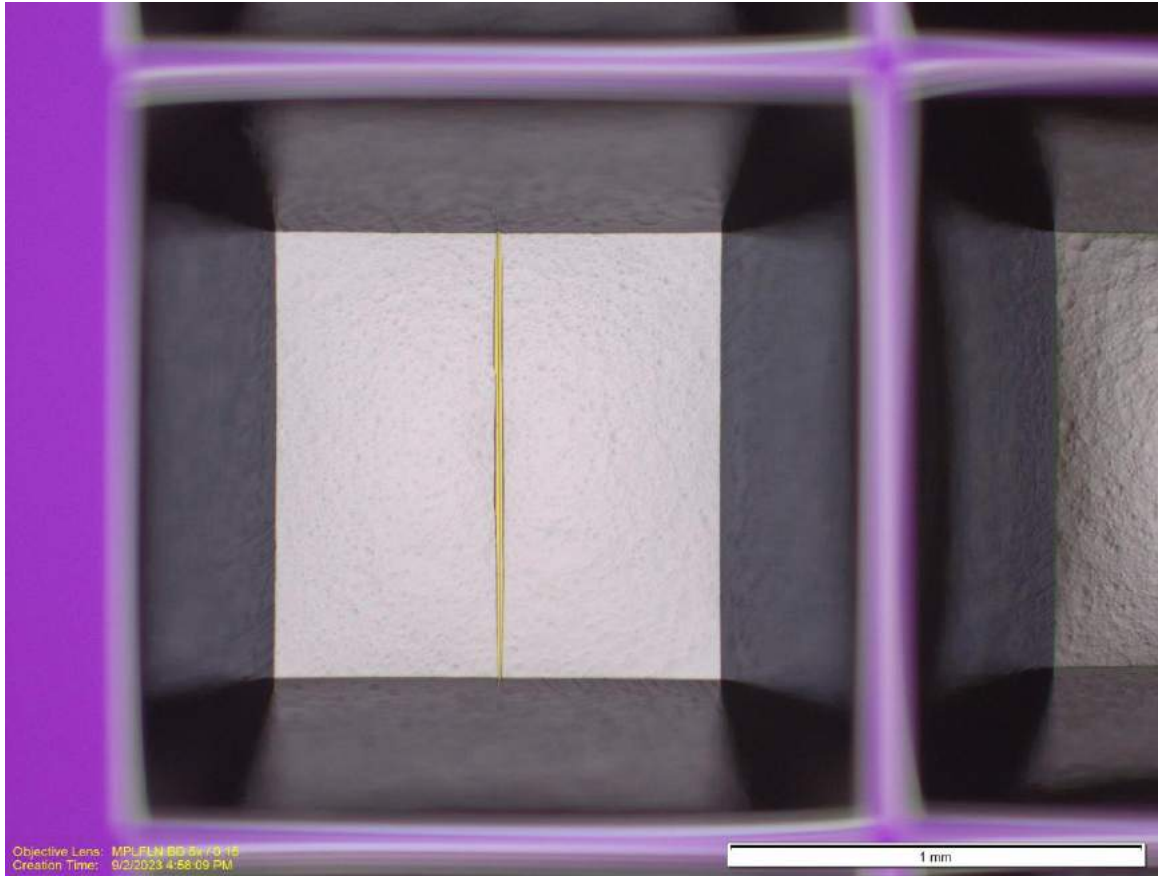
Fabrication of Shadow mask 2



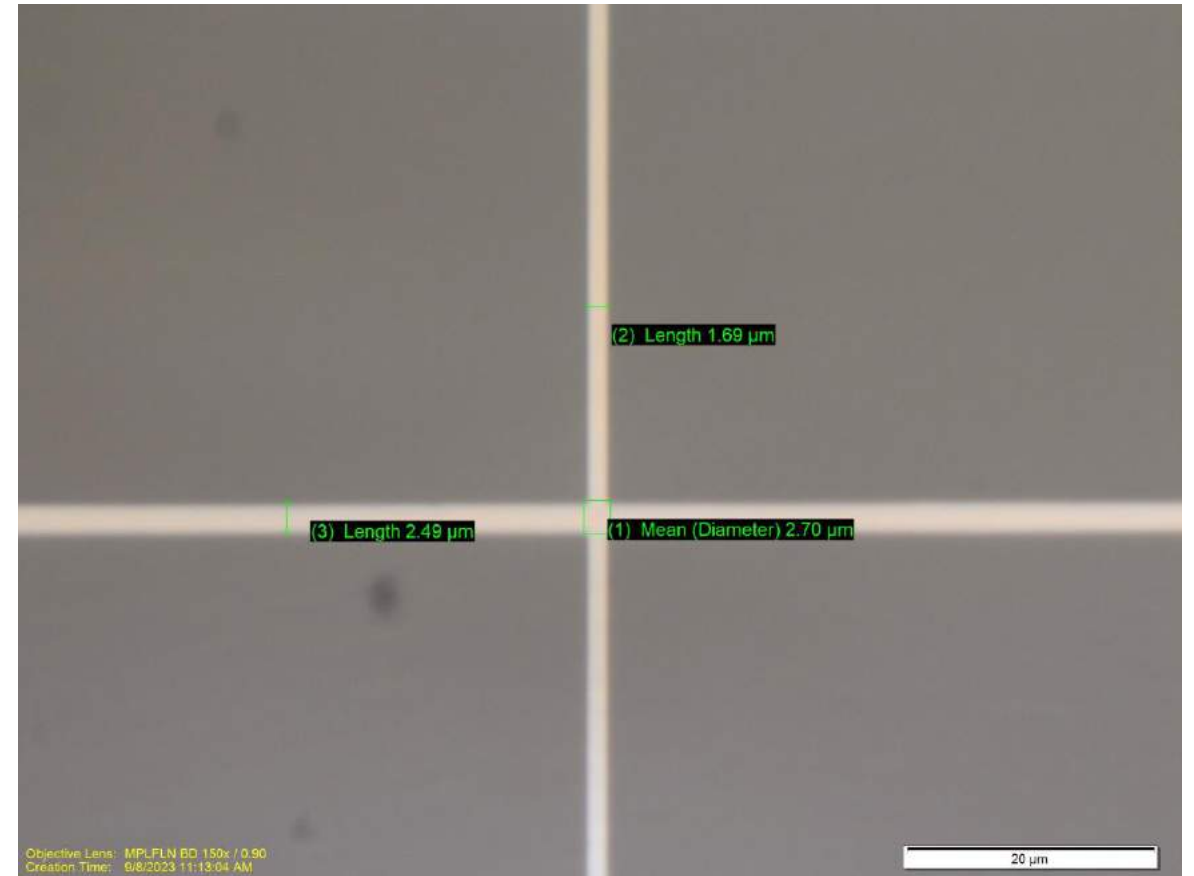
Shadow mask 3



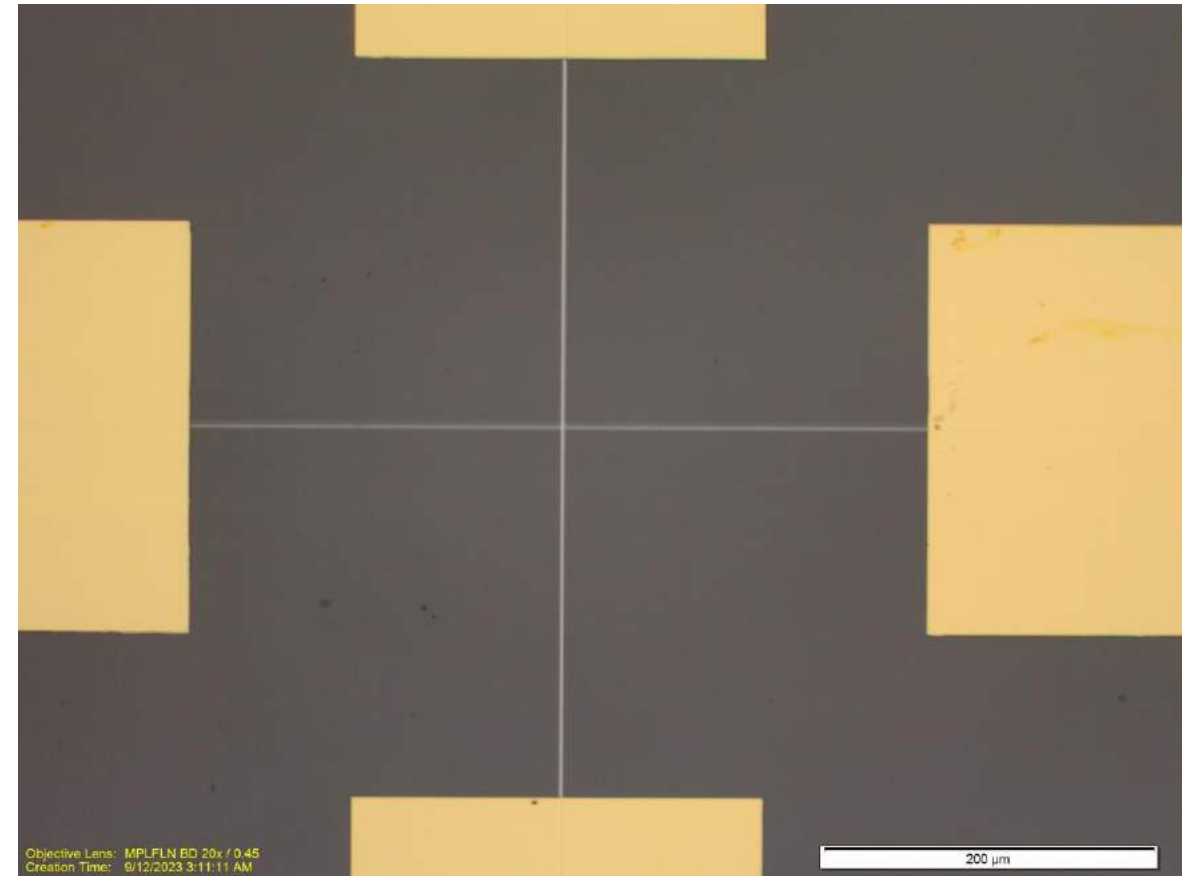
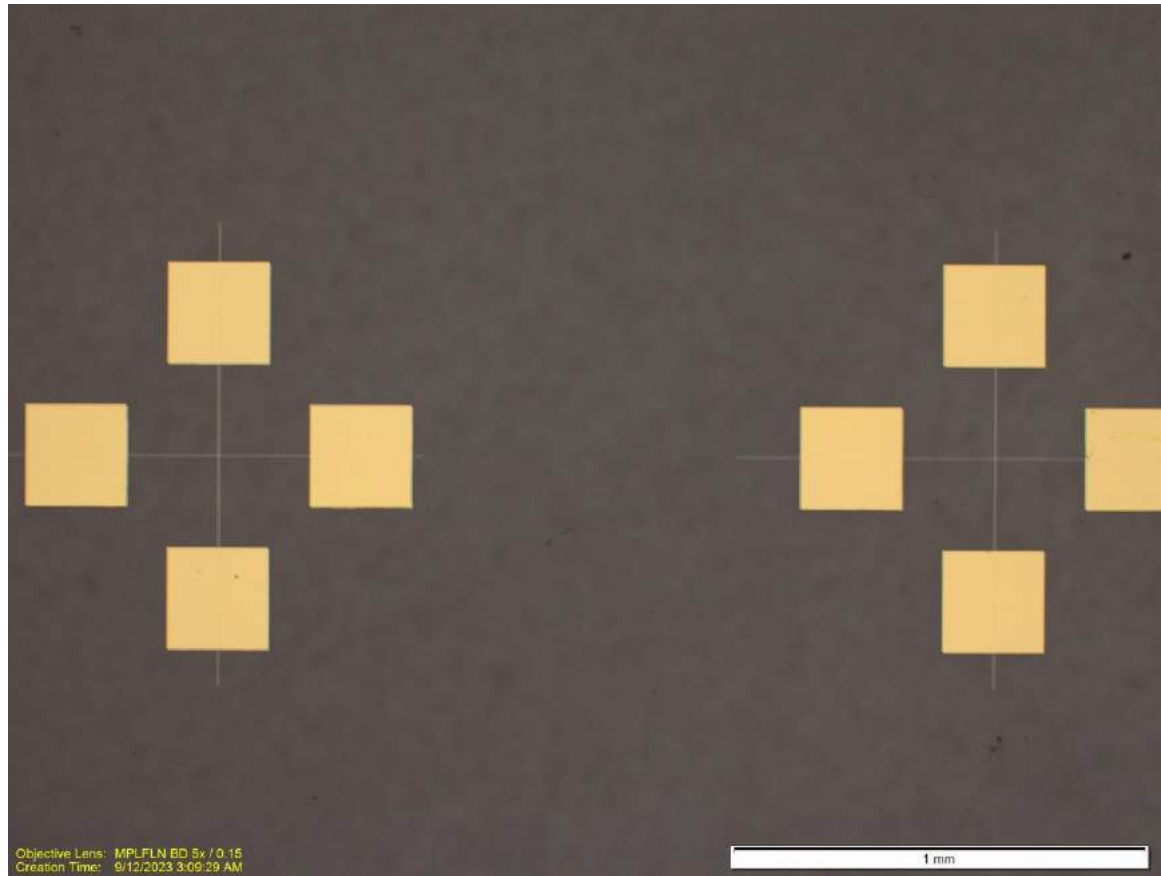
Shadow mask 3



After Growth



Final Device



UC SANTA BARBARA